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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/774,536	02/10/2004	Yuichi Sato	204552016501	204552016501 3216	
. 75	7590 02/07/2005		EXAMINER		
Barry E. Bretschneider Morrison & Foerster LLP Suite 300 1650 Tysons Boulevard			WILLE, DOUGLAS A		
			ART UNIT	PAPER NUMBER	
			2814		
McLean, VA	22102		DATE MAILED: 02/07/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
	10/774,536	SATO, YUICHI				
Office Action Summary	Examiner	Art Unit				
	Douglas A. Wille	2814				
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period w  - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days will apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	ely filed s will be considered timely. the mailing date of this communication. O (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on 10 Fe	ebruary 2004.					
	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims						
<ul> <li>4)  Claim(s) 1-9 is/are pending in the application.</li> <li>4a) Of the above claim(s) is/are withdraw</li> <li>5)  Claim(s) is/are allowed.</li> <li>6)  Claim(s) 1-9 is/are rejected.</li> <li>7)  Claim(s) is/are objected to.</li> <li>8)  Claim(s) are subject to restriction and/or</li> </ul>						
Application Papers						
9) ☐ The specification is objected to by the Examine 10) ☑ The drawing(s) filed on 10 February 2004 is/are Applicant may not request that any objection to the Replacement drawing sheet(s) including the correction 11) ☐ The oath or declaration is objected to by the Examine 11.	e: a)⊠ accepted or b)⊡ objected drawing(s) be held in abeyance. See ion is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CFR 1.121(d).				
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau * See the attached detailed Office action for a list of	s have been received. s have been received in Application rity documents have been received (PCT Rule 17.2(a)).	on No ed in this National Stage				
Attachment(s)						
1) Notice of References Cited (PTO-892)	4) Interview Summary	(PTO-413)				
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail Da	ite				
3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date <u>0204</u> .	5)  Notice of Informal P 6)  Other:	atent Application (PTO-152)				

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## **DETAILED ACTION**

## Claim Rejections - 35 USC § 103

- 1. Claims 1, 2 and 4 are rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's admitted prior art and Hu et al.
- 2. With respect to claim 1, Applicant's admitted prior art, Figure 9, shows an SRAM comprised of CMOS devices. Hu et al. show a DTMOS device (see Figure 7 and column 1, line 8 et seq.) that has the n-well deeper than the p-well and that can be used in CMOS circuitry for the advantages shown (column 2, line 46). It would have been obvious to modify the basic device to include the DTMOS device shown by Hu et al. for the advantages shown. Note that the gates are electrically connected.
- 3. With respect to claim 2, note that the gates of the devices are connected to a power supply and therefore, so are the channel forming regions.
- 4. With respect to claim 4, Hu et al. show a DTMOS device (see Figure 7 and column 1, line 8 et seq.) that has the n-well deeper than the p-well.
- 5. Claim 3 is rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's admitted prior art and Hu et al. and further in view of Tsui et al.
- 6. Tsui et al. show the use of dual thickness gate oxides with thinner gate oxides used for low voltage devices (column 1, line 14). Since DTMOS devices use lower voltages it would have been obvious to use thinner oxides for the lower voltage devices and to use normal gate oxides for other devices.
- 7. Claims 5, 6 and 9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's admitted prior art and Hu et al. and further in view of Hodges et al.

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- 8. With respect to claim 5, Hodges et al. show the formation of peripheral circuits for a memory device that use MOS structures (see page 368 and 369) and it would be obvious to use the DTMOS devices for these structures for the advantages shown.
- 9. With respect to claim 6, bit lines are shown.
- 10. With respect to claim 9, Hu et al. show a DTMOS device (see Figure 7 and column 1, line 8 et seq.) that has the n-well deeper than the p-well.
- 11. Claim 8 is rejected under 35 U.S.C. 103(a) as being unpatentable over Applicant's admitted prior art and Hu et al. and further in view of Hodges.
- 12. Hodges shows a SRAM which uses resistors as an alternative SRAM to that shown in Applicant's admitted prior art (see cover Figure) and it would be obvious to use that circuit as a design choice and to use the DTMOS devices for the advantages shown.

## Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Douglas A. Wille whose telephone number is (571) 272-1721. The examiner can normally be reached on M-F (6:15-2:45).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (703) 308-4918. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9306 for regular communications and (703) 872-9306 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

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Louglas A. Wille
Patent Examiner